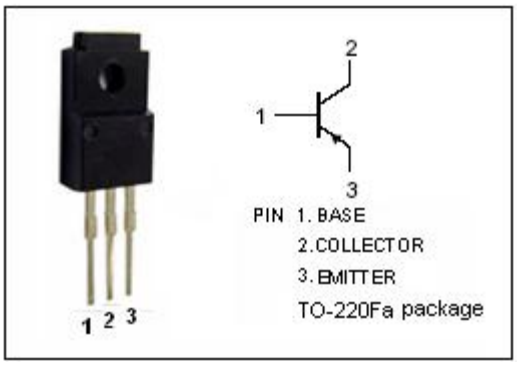
isc Silicon PNP Power Transistor 2SA1396



DESCRIPTION

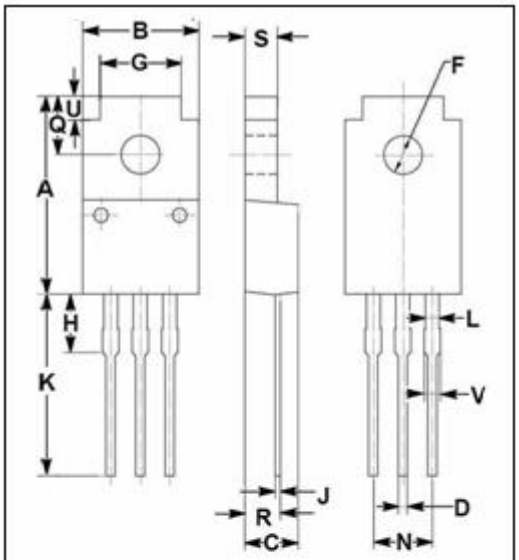
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= −0.6V(Max)@ I_C= -5A
- High Switching Speed
- Complement to Type 2SC3568
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for switching regulator, DC-DC converter and high frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-20	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -5A; I_B= -0.5A, L= 1mH	-100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A		-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A		-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0		-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-10	μA
h_{FE-1}	DC Current Gain	I_C= -0.5A; V_{CE}= -5V	40	200	
h_{FE-2}	DC Current Gain	I_C= -3A; V_{CE}= -5V	40	200	
h_{FE-3}	DC Current Gain	I_C= -5A; V_{CE}= -5V	20		

◆ **h_{FE-2} Classifications**

M	L	K
40-80	60-120	100-200